

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A)	Q _g (Typ.)						
- 20	$0.018 \text{ at V}_{GS} = -4.5 \text{ V}$	- 12 ^a							
	0.026 at $V_{GS} = -2.5 \text{ V}$	- 12 ^a	20 nC						
	0.065 at V _{GS} = - 1.8 V	- 4							

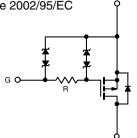
PowerPAK SC-70-6L-Single

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % $\rm R_{\rm g}$ Tested Built in ESD Protection with Zener Diode
- Typical ESD Performance: 1800 V
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

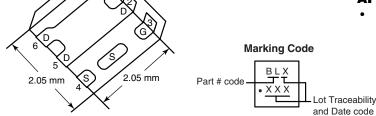
- Portable Devices
 - Load Switch
 - Battery Switch
 - Charger Switch



P-Channel MOSFET

HALOGEN

FREE



Ordering Information: SiA433EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	- 20	V		
Gate-Source Voltage		V_{GS}	± 12	v		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 ^{\circ}C$ $T_{C} = 70 ^{\circ}C$ $T_{A} = 25 ^{\circ}C$ $T_{A} = 70 ^{\circ}C$	I _D	- 12 ^a - 12 ^a - 11.3 ^{b, c} - 9.1 ^{b, c}	A		
Pulsed Drain Current		I _{DM}	- 50			
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	- 12 ^a - 2.9 ^{b, c}			
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	19 12 3.5 ^{b, c} 2.2 ^{b, c}	w		
Operating Junction and Storage Temperature R	ange	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperatur	e) ^{d, e}		260			

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5					

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 80 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 12		m\//°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	i _D = - 250 μA		3		mV/°C		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.5		- 1.2	V		
Oata Oassaa Laaka sa	1	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 20			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5	μΑ		
Zara Cata Valtaga Drain Current		V _{DS} = - 20 V, V _{GS} = 0 V			- 1			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α		
		V _{GS} = - 4.5 V, I _D = - 7.6 A		0.015	0.018	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -6.3 \text{ A}$		0.021	0.026			
		$V_{GS} = -1.8 \text{ V}, I_D = -2.5 \text{ A}$		0.040	0.065			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 7.6 A		35		S		
Dynamic ^b				L				
Total Gate Charge		V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 11 A		50	75	nC		
0.1.0	Q_g			20	30			
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -11 \text{ A}$		3.3				
Gate-Drain Charge	Q_{gd}			8.4				
Gate Resistance	R_g	f = 1 MHz	0.2	1	2	kΩ		
Turn-On Delay Time	t _{d(on)}			0.71	1.1			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1 Ω		1.7	2.6	-		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		6	9			
Fall Time	t _f			3.2	5			
Turn-On Delay Time	t _{d(on)}			0.3	0.45	us		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1 Ω		0.6	0.9	- - -		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 9 A, V_{GEN} = - 10 V, R_g = 1 Ω		10	15			
Fall Time	t _f			3.5	5.5			
Drain-Source Body Diode Characterist	ics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 12	۸		
Pulse Diode Forward Current	I _{SM}				- 50	Α		
Body Diode Voltage	V _{SD}	I _S = - 9 A, V _{GS} = 0 V		- 0.85	- 1.2	٧		
Body Diode Reverse Recovery Time	t _{rr}			30	60	ns		
Body Diode Reverse Recovery Charge	Q _{rr}	L 0.4 dl/dt 100.4/:- T 05.00		20	40	nC		
Reverse Recovery Fall Time	t _a	$I_F = 9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		13				
Reverse Recovery Rise Time	t _b			17		ns		

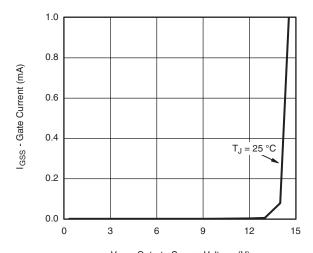
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

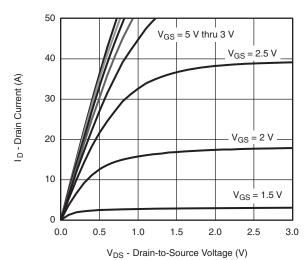


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

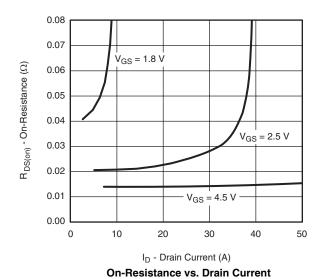


V_{GS} - Gate-to-Source Voltage (V)

Gate Current vs. Gate-Source Voltage

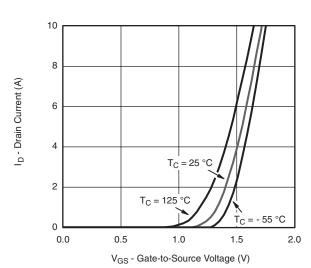


Output Characteristics

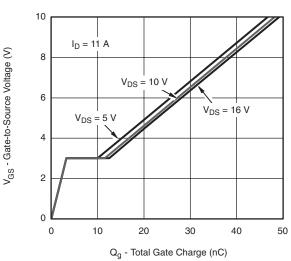


10-2 10-3 10-4 10-5 10-6 10-6 10-7 10-8 10-9 0 3 6 9 12 15 V_{GS} - Gate-to-Source Voltage (V)

Gate Current vs. Gate-Source Voltage



Transfer Characteristics



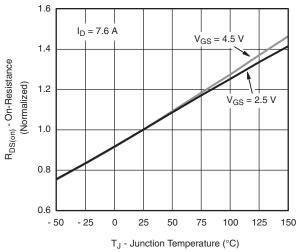
Gate Charge

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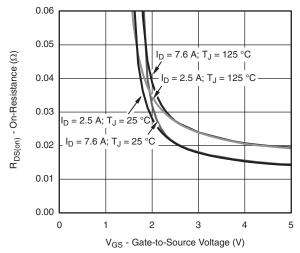
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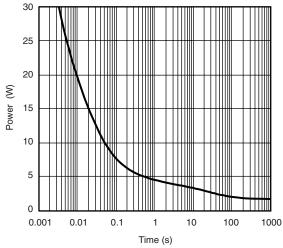
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



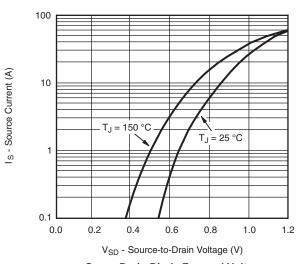
On-Resistance vs. Junction Temperature



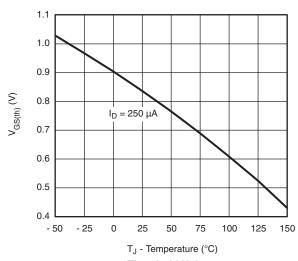
On-Resistance vs. Gate-to-Source Voltage



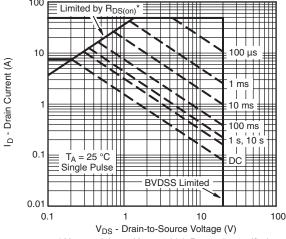
Single Pulse Power, Junction-to-Ambient



Soure-Drain Diode Forward Voltage



Threshold Voltage



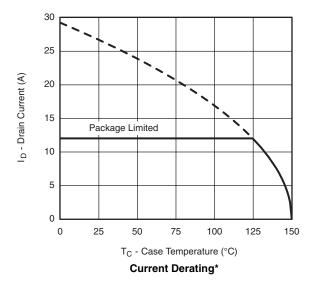
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

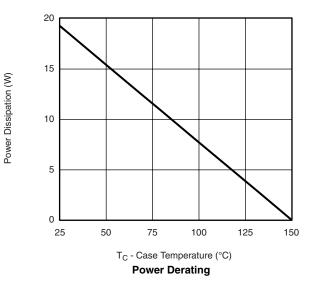
Safe Operating Area, Junction-to-Ambient





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





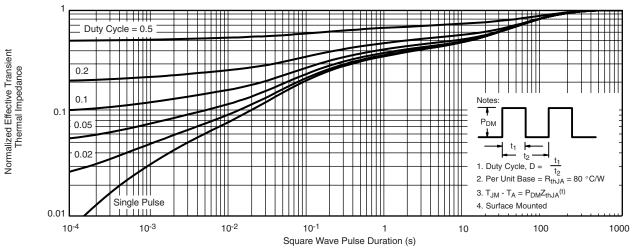
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

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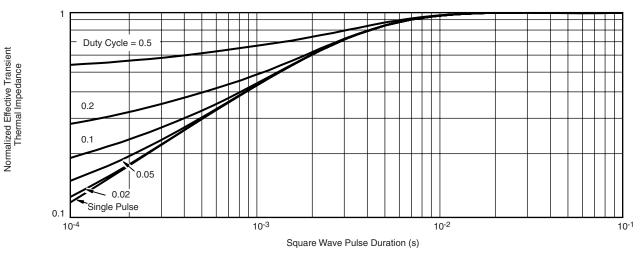
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Normalized Thermal Transient Impedance, Junction-to-Ambient



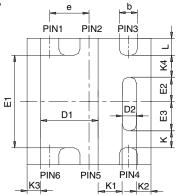
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65472.





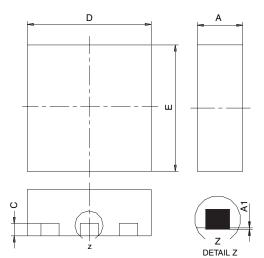
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

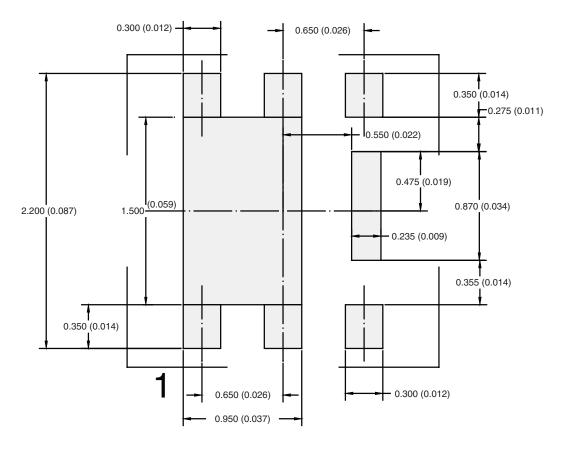
	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP	١	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP			1				
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
FCN: C-07431 - Rev. C. 06-Aug-07												

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Revision: 02-Oct-12 Document Number: 91000

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IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

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